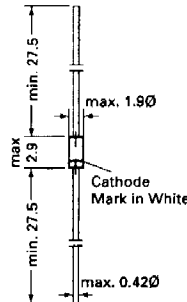


1N 4148M
SILICON EPITAXIAL PLANAR DIODE

Silicon Epitaxial Planar Diode
 fast switching diode.



Glass case JEDEC DO-34

Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Peak Reverse Voltage	V_{RM}	60	V
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb} = 25^\circ\text{C}$ and $f \geq 50$ Hz	I_o	130 ¹⁾	mA
Surge Forward Current at $t < 1$ s and $T_j = 25^\circ\text{C}$	I_{FSM}	500	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	400 ¹⁾	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to + 200	$^\circ\text{C}$

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

Characteristics at $T_j = 25^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100$ mA	V_F	-	-	1.1	V
Leakage Current at $V_R = 50$ V	I_R	-	-	0.5	μA
Reverse Breakdown Voltage tested with 100 μA Pulses	$V_{(BR)R}$	60	-	-	V
Capacitance at $V_F = V_R = 0$	C_{tot}	-	-	3	pF
Reverse Recovery Time from $I_F = 10$ mA to $I_R = 1$ mA, $V_R = 6$ V, $R_L = 100 \Omega$,	t_{rr}	-	-	4	ns

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature